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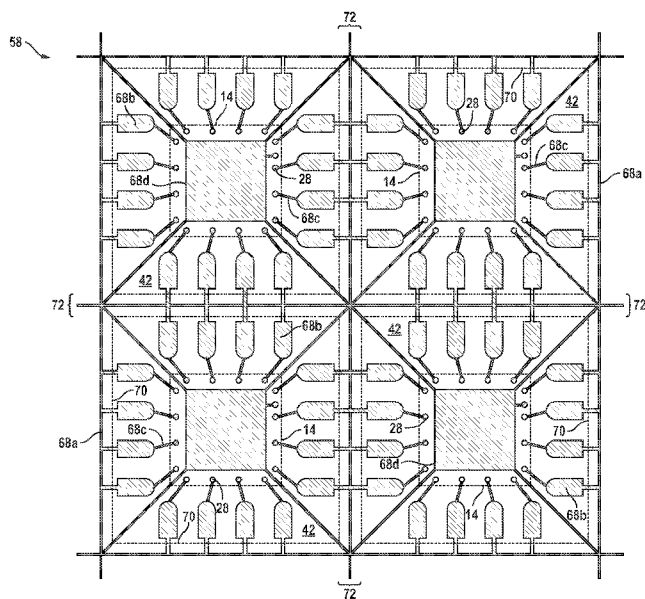
(54) **Title:** SEMICONDUCTOR DEVICE AND METHOD OF MAKING SEMICONDUCTOR DEVICE

FIG. 2M

(57) **Abstract:** A semiconductor device and method of making a semiconductor device is described. An embedded die panel comprising a plurality of semiconductor die separated by saw streets is provided. A conductive layer is formed by an electroless plating process, the conductive layer comprising bussing lines disposed in the saw streets and a redistribution layer (RDL) coupled to the semiconductor die and bussing lines. An insulating layer is formed over the conductive layer and embedded die panel, the insulating layer comprising openings disposed over the conductive layer outside a footprint of the semiconductor die. Interconnect structures are formed in the openings in the insulating layer by using the conductive layer as part of an electroplating process. The embedded die panel is singulated through the saw streets after forming the interconnect structures to remove the bussing lines and to form individual fan-out wafer level packages.